Advance Information

The RF Small Signal Line **Silicon Lateral FET**

N-Channel Enhancement-Mode MOSFET

Designed for use in low voltage, moderate power amplifiers such as portable analog and digital cellular radios and PC RF modems.

- Performance Specifications at 6 Volt, 850 MHz: Output Power = 31.5 dBm Min Power Gain = 8.5 dB Typ Efficiency = 60% Min
- Guaranteed Ruggedness at Load VSWR = 20:1
- Available in Tape and Reel Packaging Options:
 T1 Suffix = 1,000 Units per Reel
- MXR9745RT1 is Gate—Drain Pin Out Reversed. All Electricals Same as MXR9745T1

MXR9745T1 MXR9745RT1

31.5 dBm, 850 MHz HIGH FREQUENCY POWER TRANSISTOR LDMOS FET



CASE 345-03 (MXR9745RT1, STYLE 8) (MXR9745T1, STYLE 9) (SOT-89)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	VDSS	35	Vdc
Drain–Gate Voltage (R _{GS} = 1 M Ω)	V _{DGO}	25	Vdc
Gate-Source Voltage	VGS	±10	Vdc
Drain Current – Continuous	ΙD	2	Adc
Total Device Dissipation @ T _C = 50°C Derate above 50°C	PD	10 100	W mW/°C
Storage Temperature Range	T _{stg}	- 65 to +150	
Operating Junction Temperature	TJ	150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	10	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					_
Drain–Source Leakage Current (V _{DS} = 35 V, V _{GS} = 0)	IDSS	_	_	10	μAdc
Gate-Source Leakage Current (VGS = 5 V, VDS = 0)	l _{GSS}	-	_	1	μAdc

NOTE – <u>CAUTION</u> – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



ELECTRICAL CHARACTERISTICS – continued ($T_C = 25$ °C unless otherwise noted)

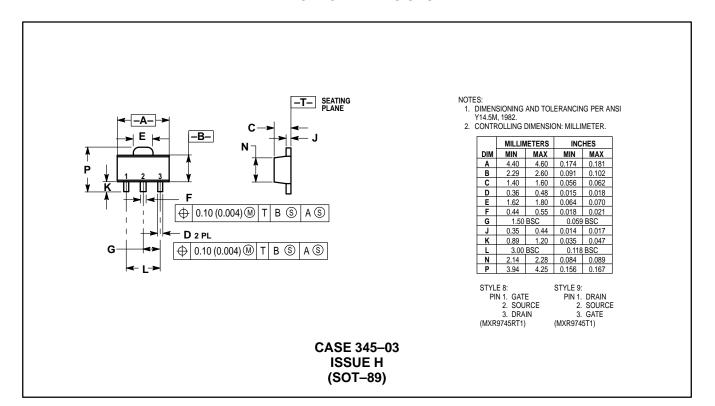
Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS	•				•
Gate Threshold Voltage (VDS = 6 V, ID = 500 μ A)	VGS(th)	1	1.3	2	Vdc
Forward Transconductance (V _{DS} = 6 V, I _D = 400 mA)	9fs	-	550	-	mmhos
Resistance Drain–Source (V _{GS} = 4 V, I _D = 100 mA)	R _{DS(on)}	-	1	2.5	Ω
DYNAMIC CHARACTERISTICS	•		•		•
Input Capacitance (V _{DS} = 6 V, V _{GS} = 0, f = 1 MHz)	C _{iss}	-	14	-	pF
Output Capacitance (V _{DS} = 6 V, V _{GS} = 0, f = 1 MHz)	C _{oss}	-	11	_	pF
Feedback Capacitance (V _{DS} = 6 V, V _{GS} = 0, f = 1 MHz)	C _{rss}	-	1.8	-	pF
FUNCTIONAL CHARACTERISTICS	•		•		•
Power Gain (V _{DD} = 6 Vdc, P _{in} = 23 dBm, I _{DQ} = 250 mA, f = 850 MHz)	G _{ps}	8	8.5	-	dB
Drain Efficiency (V _{DD} = 6 Vdc, P _{in} = 23 dBm, I _{DQ} = 250 mA, f = 850 MHz)	ηD	55	60	_	%
Ruggedness Test (VDD = 6 Vdc, Pin = 23 dBm, IDQ = 250 mA, f = 850 MHz, Load VSWR = 20:1, All Phase Angles at Frequency Test)	Ψ	No Degradation in Output Power after Test			

Table 1. Large Signal Impedance V_{DD} = 6 V, P_{in} = 23 dBm, I_{DQ} = 250 mA

f	Z _{in}	Z _{OL} *
MHz	Ohms	Ohms
850	4.8 – j6.4	6 – j7.5

Z_{OL}* is the conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

PACKAGE DIMENSIONS



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